



STB19NB20

N - CHANNEL ENHANCEMENT MODE PowerMESH™ MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|-----------|------------------|---------------------|----------------|
| STB19NB20 | 200 V | < 0.180 Ω | 19 A |

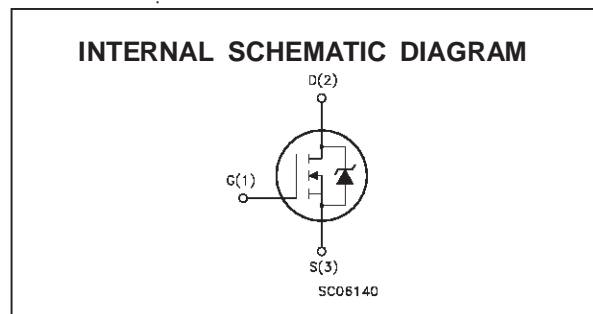
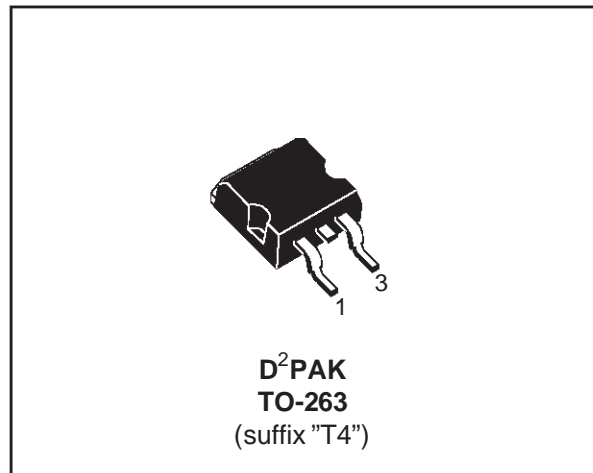
- TYPICAL R_{DS(on)} = 0.150 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of Power MOSFETs with outstanding performance. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|---|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 200 | V |
| V _{DGR} | Drain- gate Voltage (R _{GS} = 20 kΩ) | 200 | V |
| V _{GS} | Gate-source Voltage | ± 30 | V |
| I _D | Drain Current (continuous) at T _c = 25 °C | 19 | A |
| I _D | Drain Current (continuous) at T _c = 100 °C | 12 | A |
| I _{DM} (●) | Drain Current (pulsed) | 76 | A |
| P _{tot} | Total Dissipation at T _c = 25 °C | 125 | W |
| | Derating Factor | 1 | W/°C |
| dv/dt(1) | Peak Diode Recovery voltage slope | 5.5 | V/ns |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 19A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

STB19NB20

THERMAL DATA

| | | | | |
|-----------------------|--|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-case | Max | 1 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-ambient | Max | 62.5 | °C/W |
| R _{thc-sink} | Thermal Resistance Case-sink | Typ | 0.5 | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | | 300 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max) | 19 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 580 | mJ |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|--|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA V _{GS} = 0 | 200 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C | | | 1 10 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 30 V | | | ± 100 | nA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|-------|-------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} I _D = 250 μA | 3 | 4 | 5 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V I _D = 9.5 A | | 0.150 | 0.180 | Ω |
| I _{D(on)} | On State Drain Current | V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V | 19 | | | A |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g _{fs} (*) | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 9.5 A | 3 | | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25 V f = 1 MHz V _{GS} = 0 | | 1000 | 1350 | pF |
| C _{oss} | Output Capacitance | | | 285 | 385 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 45 | 60 | pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on Time | $V_{DD} = 100\text{ V}$ $I_D = 9.5\text{ A}$ | | 15 | 20 | ns |
| t_r | Rise Time | $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3) | | 15 | 20 | ns |
| Q_g | Total Gate Charge | $V_{DD} = 160\text{ V}$ $I_D = 19\text{ A}$ $V_{GS} = 10\text{ V}$ | | 29 | 40 | nC |
| Q_{gs} | Gate-Source Charge | | | 9.5 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 13 | | nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|--|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 160\text{ V}$ $I_D = 19\text{ A}$ | | 10 | 15 | ns |
| t_f | Fall Time | $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5) | | 10 | 15 | ns |
| t_c | Cross-over Time | | | 20 | 30 | ns |

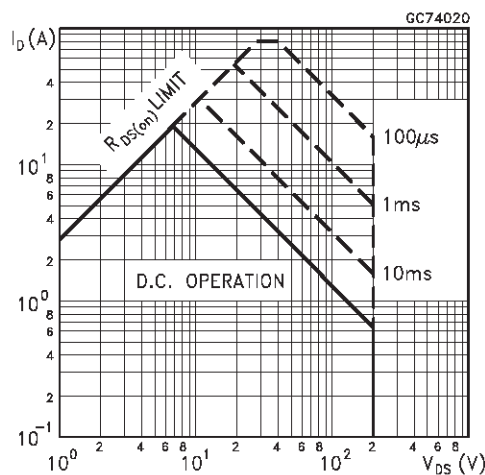
SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------------|-------------------------------|---|------|------|------|---------------|
| I_{SD} | Source-drain Current | | | | 19 | A |
| $I_{SDM}(\bullet)$ | Source-drain Current (pulsed) | | | | 76 | A |
| $V_{SD}(\ast)$ | Forward On Voltage | $I_{SD} = 19\text{ A}$ $V_{GS} = 0$ | | | 1.5 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 19\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5) | | 210 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 1.5 | | μC |
| I_{RRM} | Reverse Recovery Current | | | 14.5 | | A |

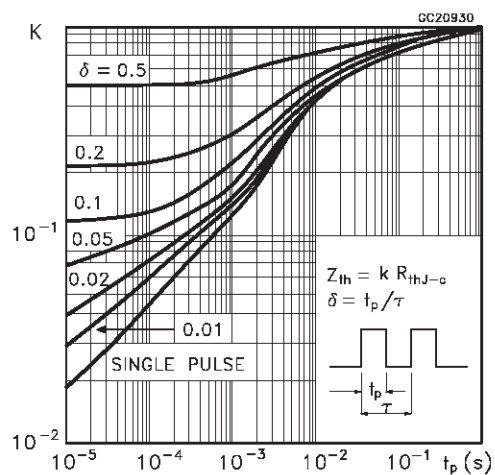
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

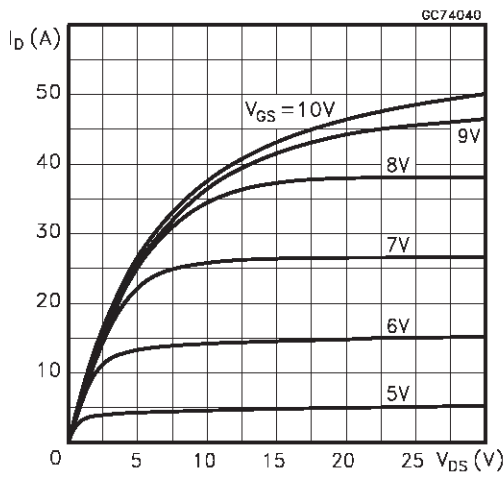
Safe Operating Area



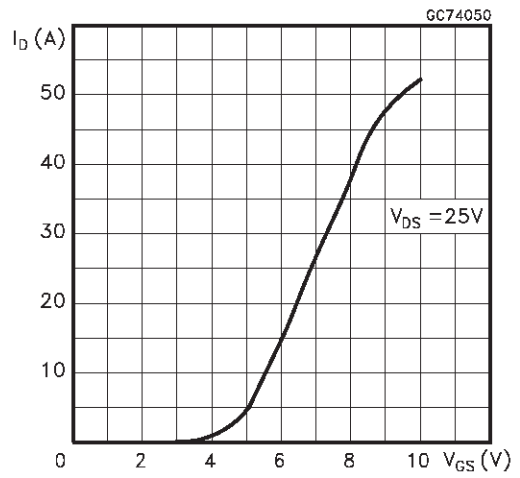
Thermal Impedance



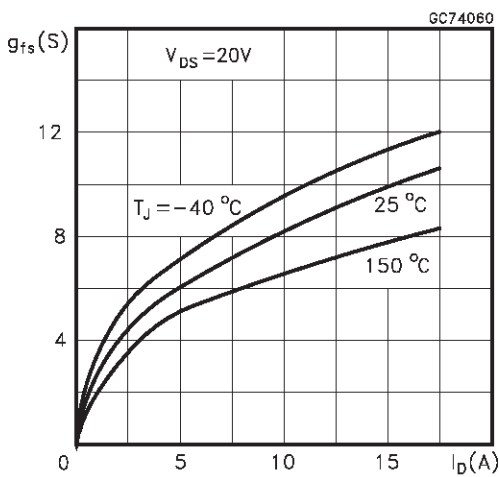
Output Characteristics



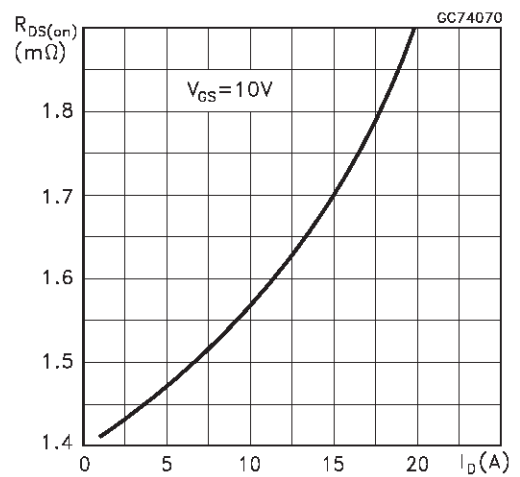
Transfer Characteristics



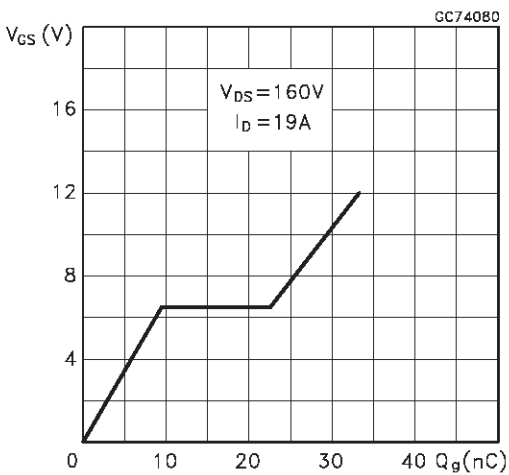
Transconductance



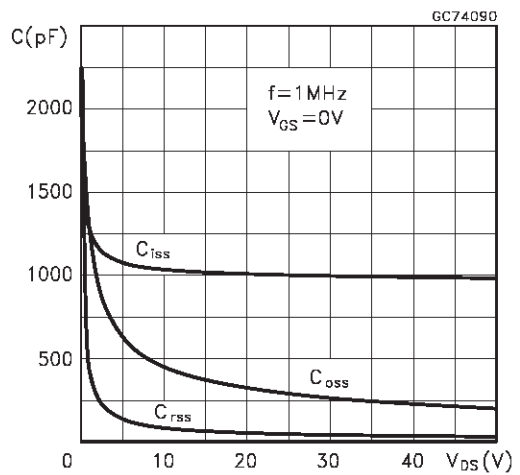
Static Drain-source On Resistance



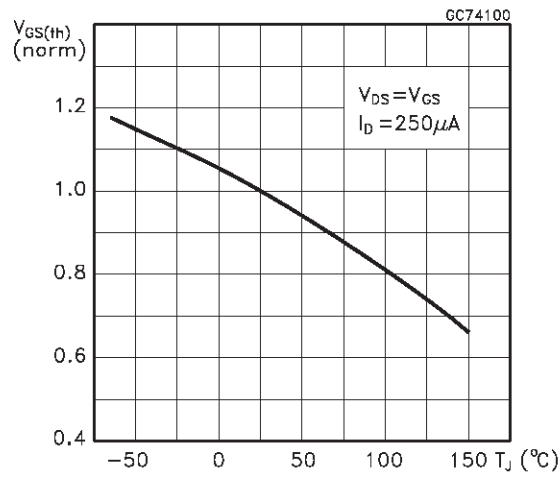
Gate Charge vs Gate-source Voltage



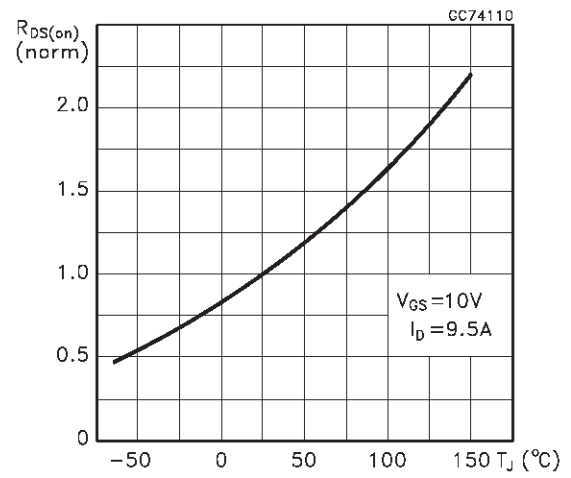
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

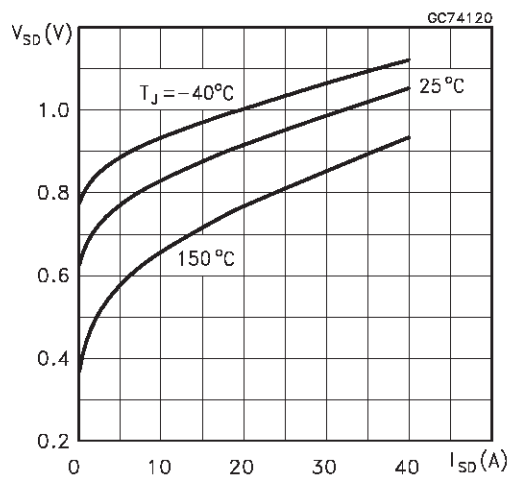


Fig. 1: Unclamped Inductive Load Test Circuit

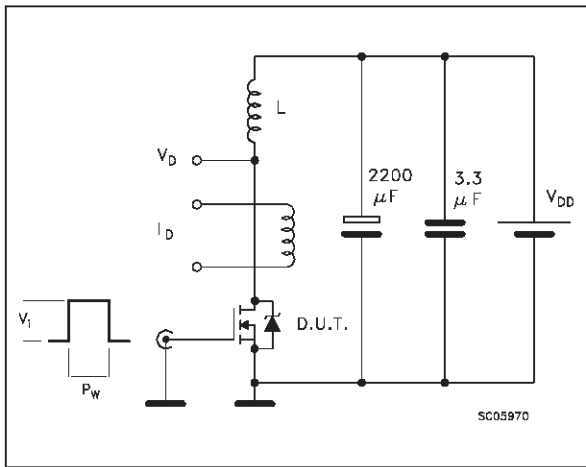


Fig. 2: Unclamped Inductive Waveform

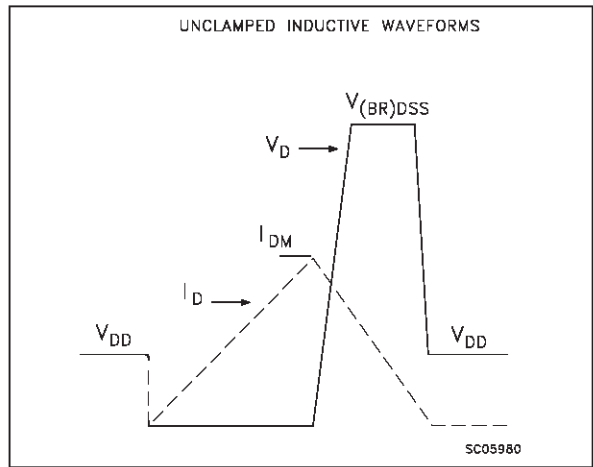


Fig. 3: Switching Times Test Circuits For Resistive Load

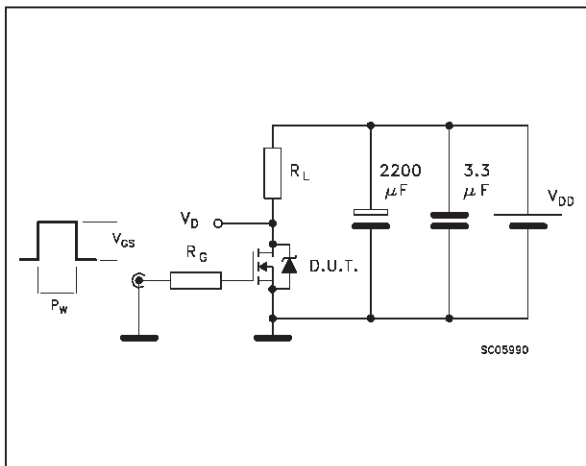


Fig. 4: Gate Charge test Circuit

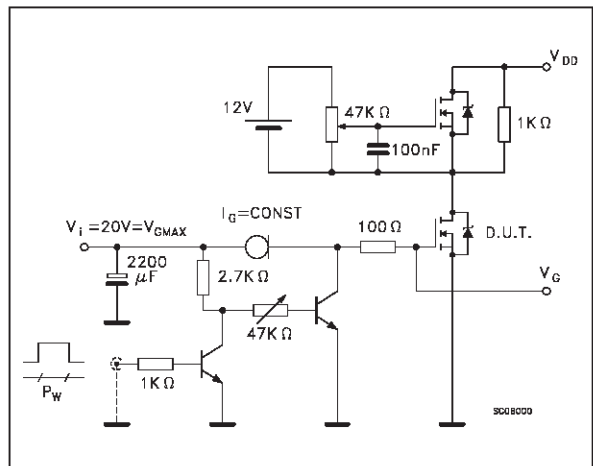
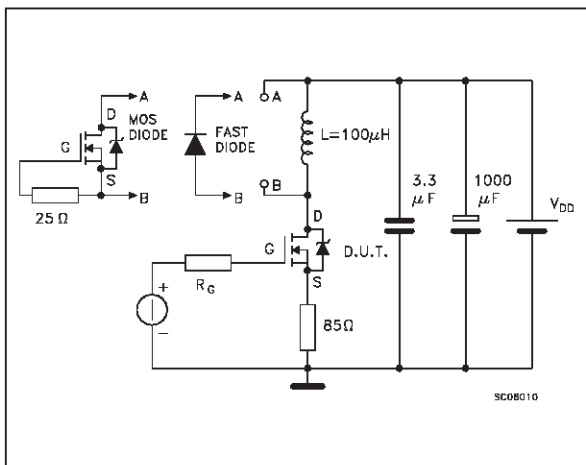
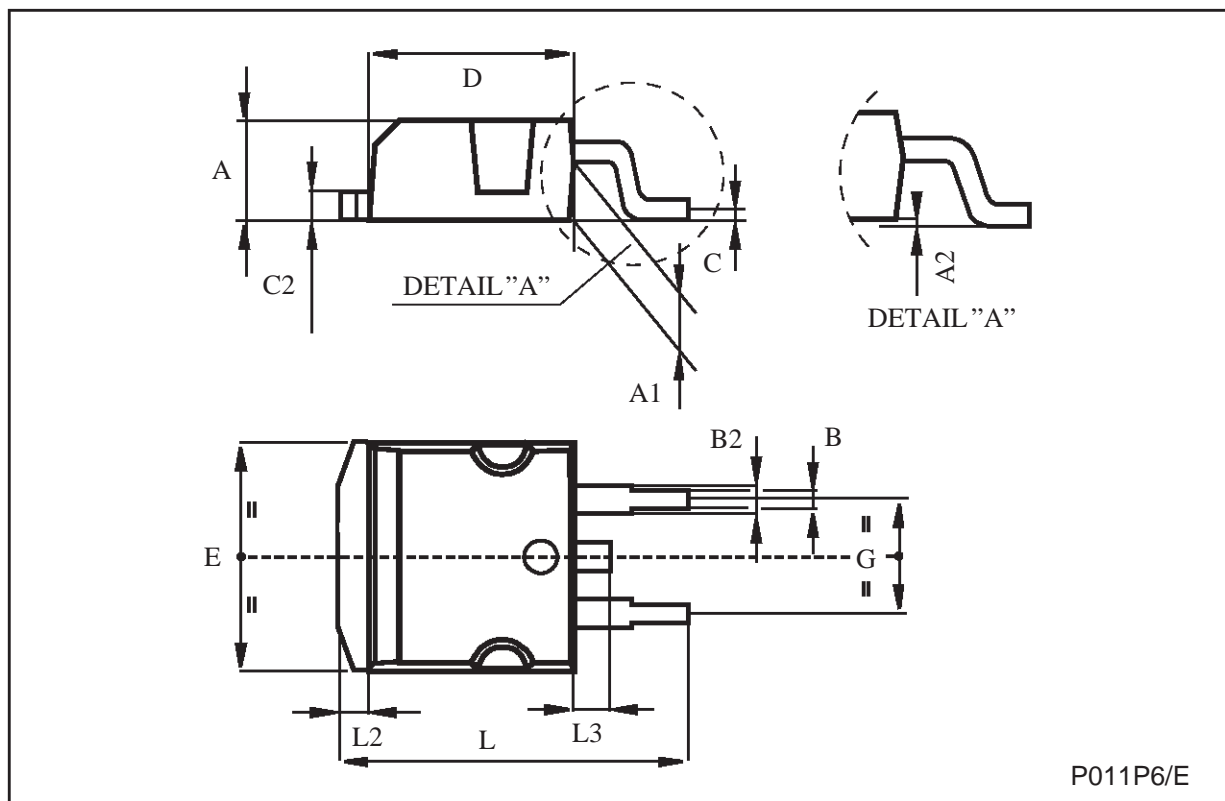


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-263 (D²PAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|-------|-------|------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| A1 | 2.49 | | 2.69 | 0.098 | | 0.106 |
| B | 0.7 | | 0.93 | 0.027 | | 0.036 |
| B2 | 1.14 | | 1.7 | 0.044 | | 0.067 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 1.21 | | 1.36 | 0.047 | | 0.053 |
| D | 8.95 | | 9.35 | 0.352 | | 0.368 |
| E | 10 | | 10.4 | 0.393 | | 0.409 |
| G | 4.88 | | 5.28 | 0.192 | | 0.208 |
| L | 15 | | 15.85 | 0.590 | | 0.624 |
| L2 | 1.27 | | 1.4 | 0.050 | | 0.055 |
| L3 | 1.4 | | 1.75 | 0.055 | | 0.068 |



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